

Title (en)

Thin film semiconductor device

Title (de)

Dünnschicht-Halbleiterbauelement

Title (fr)

Dispositif semi-conducteur à film mince

Publication

EP 0449598 B1 19960313 (EN)

Application

EP 91302658 A 19910326

Priority

- JP 7840390 A 19900327
- JP 7840490 A 19900327
- JP 7840690 A 19900327

Abstract (en)

[origin: EP0449598A2] A thin film semiconductor device includes a gate electrode (401), a gate insulating layer (402), a thin film semiconductor layer (403), an ohmic layer (406) source and drain electrodes (404,405) and a protective layer (409). The protective layer contains an impurity for controlling conductivity. <IMAGE>

IPC 1-7

H01L 29/786

IPC 8 full level

H01L 27/146 (2006.01); **H01L 29/786** (2006.01); **H01L 31/113** (2006.01)

CPC (source: EP US)

H01L 27/14643 (2013.01 - EP US); **H01L 29/78669** (2013.01 - EP US); **H01L 31/1136** (2013.01 - EP US)

Cited by

US7851836B2; WO2008084650A3

Designated contracting state (EPC)

AT BE CH DE DK ES FR GB GR IT LI LU NL SE

DOCDB simple family (publication)

EP 0449598 A2 19911002; EP 0449598 A3 19920108; EP 0449598 B1 19960313; AT E135496 T1 19960315; DE 69117785 D1 19960418; DE 69117785 T2 19970206; US 5576555 A 19961119; US 5705411 A 19980106

DOCDB simple family (application)

EP 91302658 A 19910326; AT 91302658 T 19910326; DE 69117785 T 19910326; US 45196895 A 19950526; US 47602695 A 19950607